

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

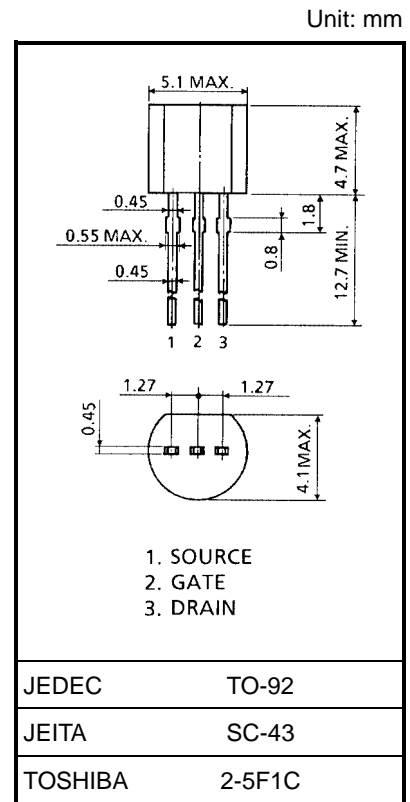
# 2SK246

For Constant Current, Impedance Converter and DC-AC High Input Impedance Amplifier Circuit Applications

- High breakdown voltage:  $V_{GDS} = -50\text{ V}$
- High input impedance:  $I_{GSS} = -1\text{ nA (max)}$  ( $V_{GS} = -30\text{ V}$ )

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	$V_{GDS}$	-50	V
Gate current	$I_G$	10	mA
Drain power dissipation	$P_D$	300	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~125	$^\circ\text{C}$



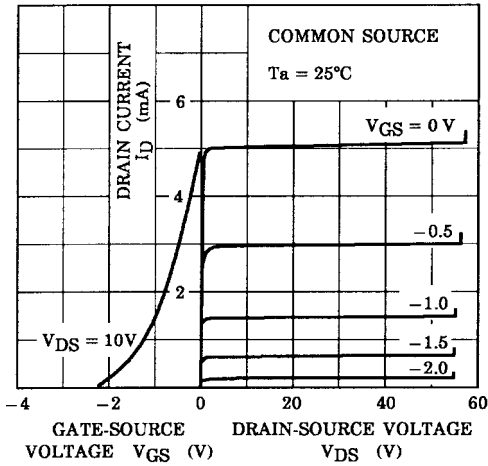
Weight: 0.21 g (typ.)

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

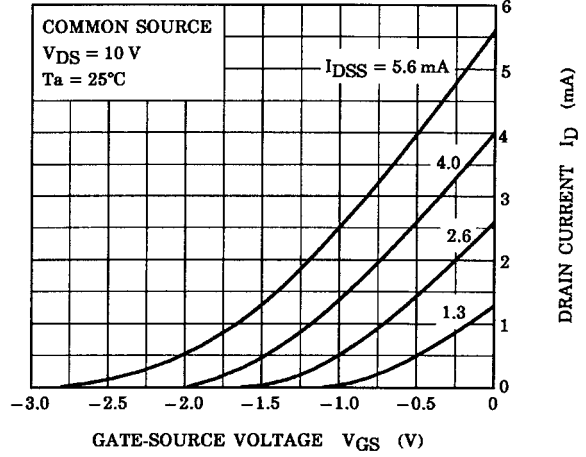
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	$I_{GSS}$	$V_{GS} = -30\text{ V}, V_{DS} = 0$	—	—	-1.0	nA
Gate-drain breakdown voltage	$V_{(BR) GDS}$	$V_{DS} = 0, I_G = -100\text{ }\mu\text{A}$	-50	—	—	V
Drain current	$I_{DSS}$ (Note)	$V_{DS} = 10\text{ V}, V_{GS} = 0$	1.2	—	14	mA
Gate-source cut-off voltage	$V_{GS (OFF)}$	$V_{DS} = 10\text{ V}, I_D = 0.1\text{ }\mu\text{A}$	-0.7	—	-6.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ kHz}$	1.5	—	—	mS
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	9.0	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DG} = 10\text{ V}, I_D = 0, f = 1\text{ MHz}$	—	2.5	—	pF

Note:  $I_{DSS}$  classification Y: 1.2~3.0 mA, GR: 2.6~6.5 mA, BL: 6~14 mA

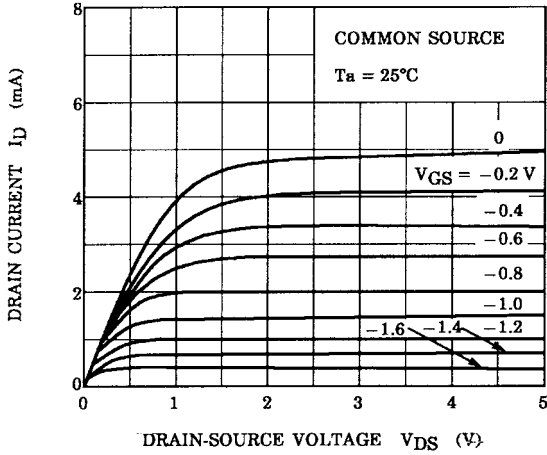
**STATIC CHARACTERISTICS**



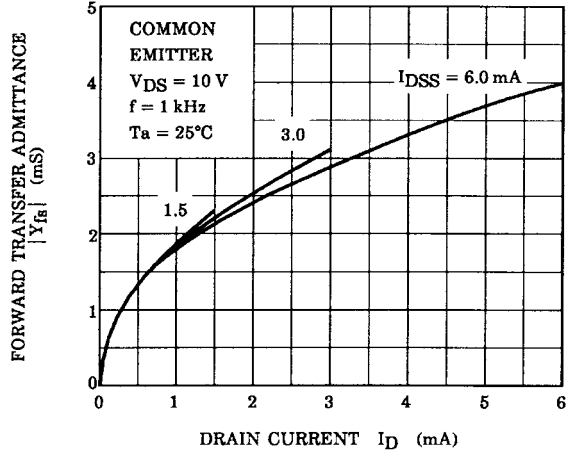
**ID - VGS**



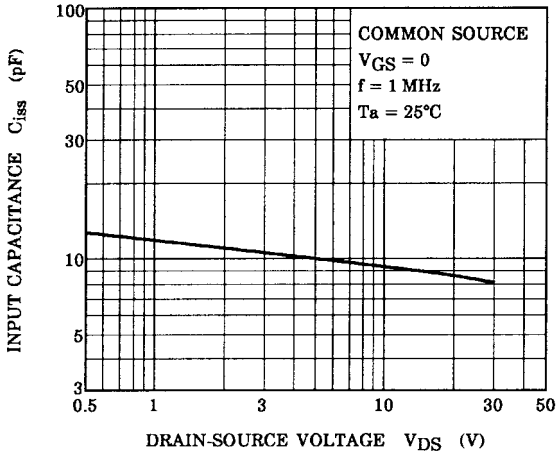
**ID - VDS (LOW VOLTAGE REGION)**



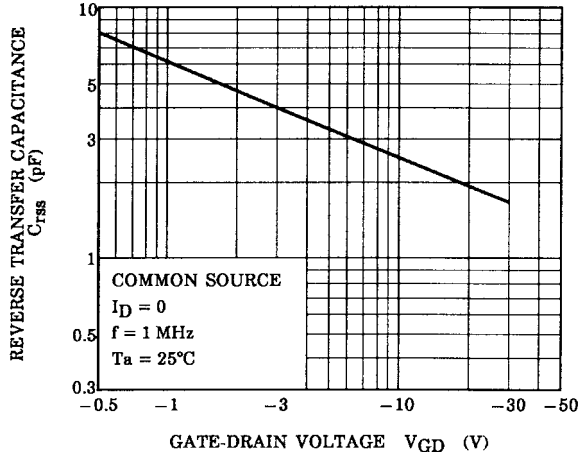
**|Yfs| - ID**

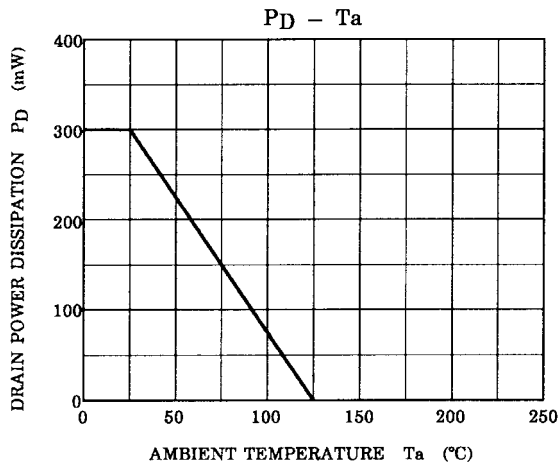
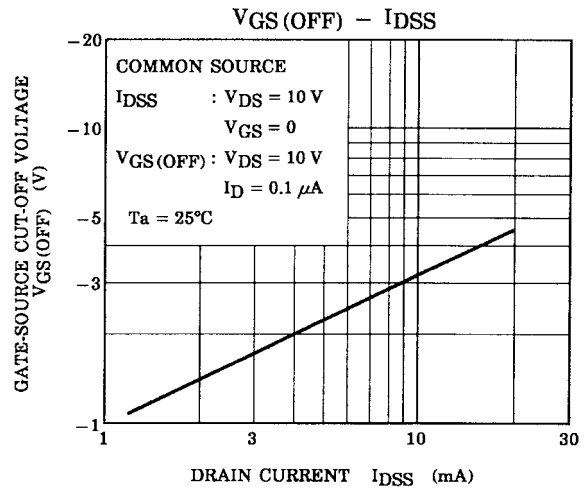
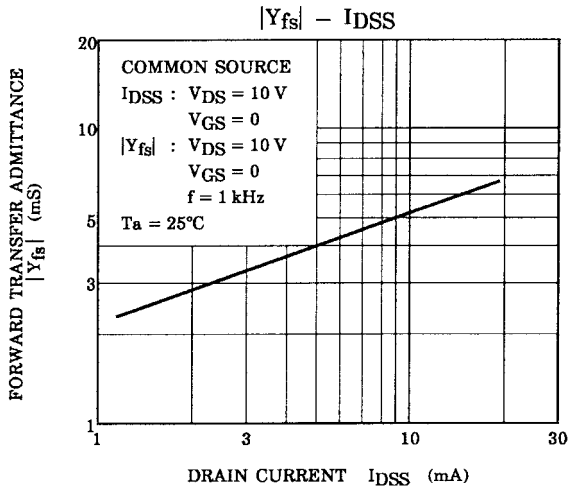


**Ciss - VDS**



**Crss - VGD**





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